风光欣技术资料

C2713

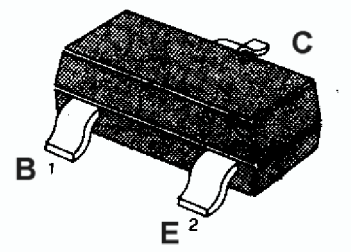
—NPN silicon —

APPLICATION: Audio Frequency General Purpose Amplifier Applications.

MAXIMUM RATINGS （Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Base current	I_B	20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	125	℃
Storage Temperature Range	T_{stg}	-55~125	℃

SOT-23



1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	200		700		V_{CE}= 6V，I_C= 2mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 120V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 5V，I_C=0
Collector-Base Breakdown Voltage	BV_{CBO}	120			V	I_C= 0.05mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	120			V	I_C= 1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E= 0.05mA，I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	I_C= 10mA，I_B= 1mA
Gain bandwidth product	f_T		100		MHz	I_C=1mA,V_{CE}=6V,f =1MHz
Common Base Output Capacitance	C_{ob}		3		pF	V_{CB}= 10V, I_E=0, f = 1MHz
Noise Figure	N_F		1	10	dB	V_{CE}=6V,I_C=0.1mA, f =1kHz,R_G=10KΩ

h_{FE} Classification And Marking

Print Mark	DG	DL
Classification	G	L
h_{FE}	200~400	350~700